

深圳市晶泰源电子有限公司

MPS2222 TRANSISTOR (NPN)

FEATURE

Power dissipation

$$P_{CM}: 0.625 \text{ W (} T_{amb}=25 \text{)}$$

Collector current

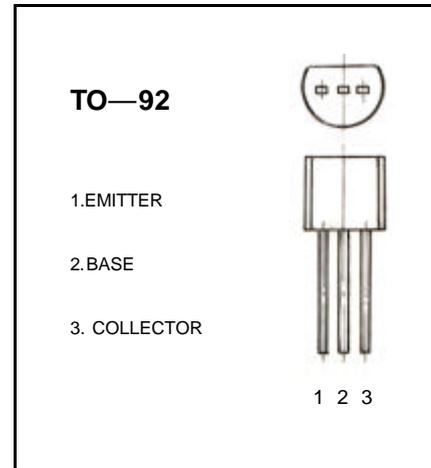
$$I_{CM}: 0.6 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55 \text{ to } +150$$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10 \mu A, I_E = 0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10 mA, I_B = 0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10 \mu A, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 50 V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3 V, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 10 V, I_C = 150 mA$	100		300	
	$h_{FE(2)}$	$V_{CE} = 10 V, I_C = 1 mA$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 mA, I_B = 50 mA$			1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500 mA, I_B = 50 mA$			2	V
Transition frequency	f_T	$V_{CE} = 20 V, I_C = 20 mA$ $f = 100 MHz$	300			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	100-200	200-300

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